





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
	7.5mΩ @ V _{GS} = 10V	30A
60V	11.5mΩ @ V _{GS} = 4.5V	25A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

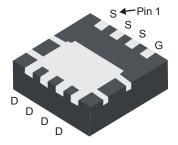
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} ensures on state losses are minimized
- Excellent Q_{gd x} R_{DS (ON)} Product (FOM)
- Advanced Technology for DC/DC converts
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free, "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

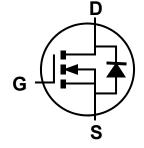
- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)







Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6010LFG-7	POWERDI [®] 3333-8	2000/Tape & Reel
DMT6010LFG-13	POWERDI®3333-8	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



SG6 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 13 = 2013) WW = Week code (01 ~ 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note EVV - 40V	T _A = +25°C T _A = +70°C	I _D	13 11	А
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	I _D	30 24	А
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	3	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	80	Α	
Avalanche Current (Note 6)	I _{AS}	20	Α	
Avalanche Energy (Note 6)	E _{AS}	64	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 5)	T _A = +25°C	D-	2.2	W	
Total Power Dissipation (Note 5)	$T_C = +25^{\circ}C$	P_D	41	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	55		
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	35	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	3			
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C		

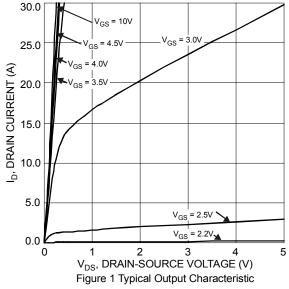
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

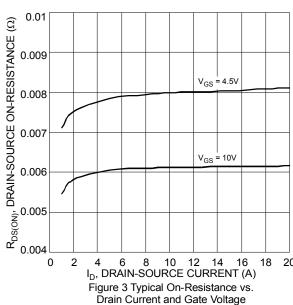
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)		_	-	_	_		
Gate Threshold Voltage	V _{GS(th)}	0.8	-	2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	l	6	7.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialii-Source Off-Resistance	R _{DS (ON)}	1	7.8	11.5		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	l	0.9	1.2	V	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	l	2090	-		V _{DS} = 30V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	746	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	38.5	_			
Gate resistance	Rg	_	0.59	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	19.3	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	41.3	_	~C	V _{DS} = 30V, I _D = 20A	
Gate-Source Charge	Qgs	_	6.0	_	nC		
Gate-Drain Charge	Q _{qd}	_	8.8	_			
Turn-On Delay Time	t _{D(on)}	_	5.7	_			
Turn-On Rise Time	t _r	_	4.3	_	~0	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	_	23.4	_	nS	$I_D = 20A, R_G = 3\Omega,$	
Turn-Off Fall Time	t _f	_	9.7	_			

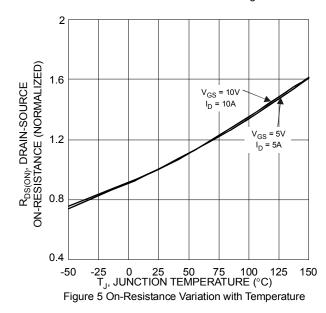
Notes:

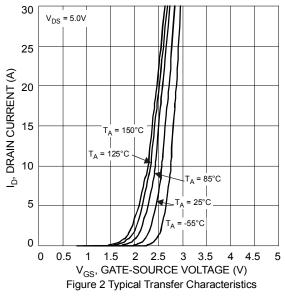
- 5. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.
- 6 .UIS in production with L = 0.3mH, T_J = +25°C
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

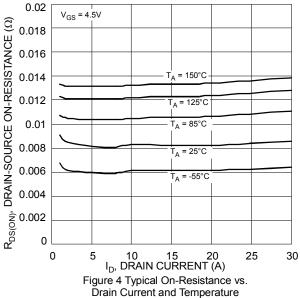


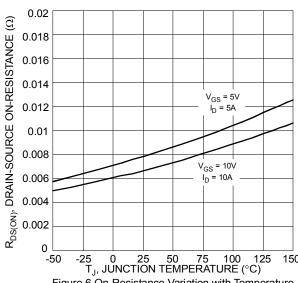












T_A = 85°C T_A = 25°C T_A = -55°C

1.5



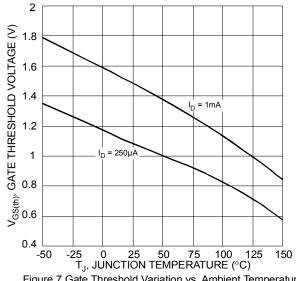
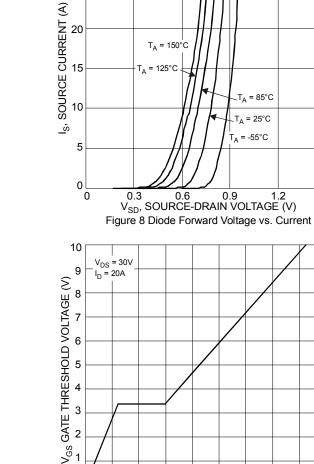


Figure 7 Gate Threshold Variation vs. Ambient Temperature



0

0 5

30

25

T_A = 150°C

20 25

Q_g, TOTAL GATE CHARGE (nC)

30

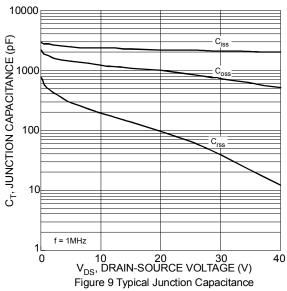
35

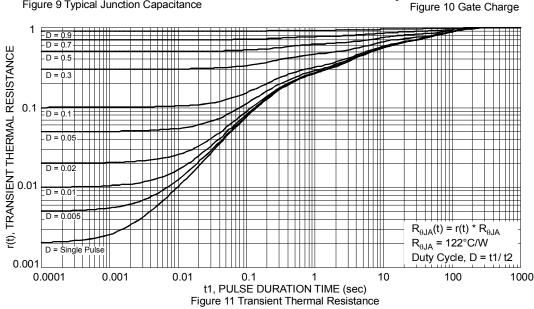
40 45

15

10

= 125°C

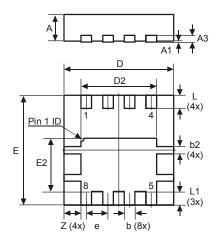






Package Outline Dimensions

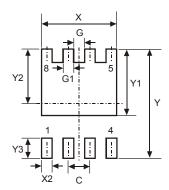
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI®3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
A3	_	-	0.203		
b	0.27	0.37	0.32		
b2	_	-	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	0.230		
G1	0.420		
Y	3.700		
Y1	2.250		
Y2	1.850		
Y3	0.700		
X	2.370		
X2	0.420		



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